

Magnetic instability induced by Rh doping in the Kondo semiconductor CeRu₂Al₁₀

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The ternary compound CeT₂Al₁₀ (T = Fe, Ru, and Os) is a unique system that shows Kondo semiconducting behavior at low temperatures, and it exhibits an antiferromagnetically (AFM) ordered state at $T_0 \sim 30$ K for T = Ru and Os, while a nonmagnetic ground state is observed for T = Fe, as is usually the case for Kondo semiconductors (or insulators).¹⁻³ Since the magnetic susceptibility (χ) systematically decreases on changing the transition metal element in the order from T = Ru to Os to Fe, the $4f$ electron state is located in the vicinity of the boundary between localized and non-localized states, as expected from the Kondo semiconducting behavior. Thus, the c - f hybridization between d - and $4f$ -electrons must play a key role for their low-temperature properties involved in the origin of the AFM order.

The AFM order is very unusual. T_0 is quite high for a usual Ce-based intermetallic compound when taking into account, for instance, the long distance of 5.2 Å between neighboring Ce ions.² The magnetic anisotropy is also unusual. Although the easy axis is the a axis with the large magnetic anisotropy ($a \gg c \gg b$), the AFM ordered moment (m_{AF}) with a magnitude of 0.3–0.4 μ_B /Ce aligns in the c -axis direction.^{4,6} Recently, the Rh-doping effect on CeRu₂Al₁₀ has been examined, where Rh ($4d^8$) has one electron more than Ru ($4d^7$).^{7,8} On the basis of the results, we infer that χ becomes more Curie–Weiss like and decreases drastically below T_0 for $H \parallel a$. These results imply that the Rh-doping breaks $m_{AF} \parallel c$ and $m_{AF} \parallel a$ is realized instead. In order to clarify the spin alignment and the critical Rh concentration x_c from a microscopic point of view, we performed zero-field μ SR on Ce(Ru_{1-x}Rh_x)₂Al₁₀ ($x = 0, 0.03, 0.05, \text{ and } 0.1$).

Figure 1 shows the temperature dependence of the internal magnetic field ($H_{\text{small}}, H_{\text{large}}$) at the muon site for Ce(Ru_{1-x}Rh_x)₂Al₁₀. Here, H_{small} (H_{large}) represents the smaller (larger) component of internal magnetic fields. For the undoped sample, H_{small} shows non-mean-field-like behavior, while H_{large} increases below T_0 and saturates to a value of about 180 G below

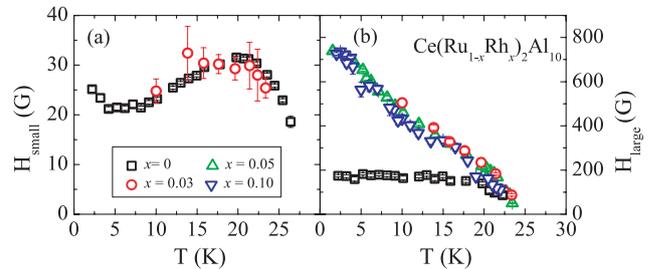


Fig. 1. Temperature dependence of the internal magnetic fields at the muon sites in Ce(Ru_{1-x}Rh_x)₂Al₁₀ ($x = 0, 0.03, 0.05, \text{ and } 0.1$): (a) H_{small} (b) H_{large} .

about 15 K. On the other hand, for Rh-doped samples, H_{large} reaches about 800 G at low temperatures. This strongly suggests the spin-flop transition from $m_{AF} \parallel c$ to $m_{AF} \parallel a$ on the basis of our dipolar field calculation at the suggested muon site, which is consistent with the bulk properties.^{7,8} Since there is no Rh-concentration dependence in H_{large} for $x > 0.03$, the boundary of the different magnetic ground states is identified at around $x \sim 0.03$. The drastic change of the magnetic ground state by such a tiny Rh doping indicates that the magnetic structure in CeRu₂Al₁₀ is not robust and can be quite easily tuned using external perturbations such as d -electron doping. On the basis of previous experimental results from thermal electric power,⁹ neutron scattering,⁴ and NQR measurements,¹⁰ the non-mean-field-like behavior of H_{small} for the $x = 0$ sample is attributed to the Fermi contact field from the polarized electrons at the muon site, while the T dependence of H_{large} for the Rh-doped samples is still an unresolved question; whether it results from the Fermi contact field or from the unusual ordering of Ce³⁺ moments should be clarified by future neutron scattering experiments.

References

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